RF POWER VDMOS TRANSISTOR

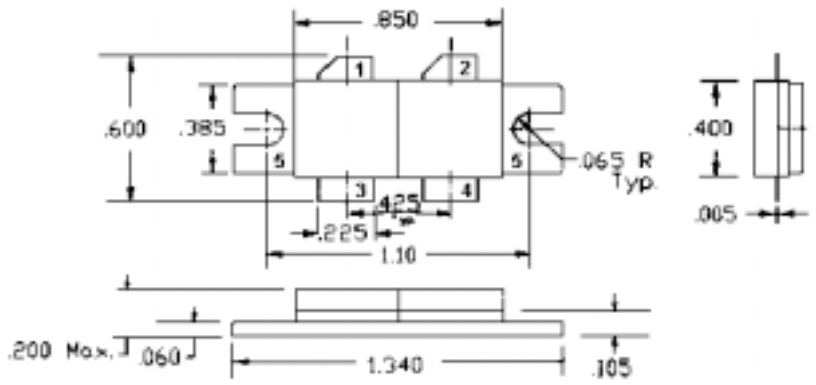
DESCRIPTION:

The **ASI BLF368** is a Dual Common Source N-Channel Enhancement-Mode VDMOS. designed for RF Applications.

MAXIMUM RATINGS

I_D	27 A
V_{DSS}	70 V
V_{GS}	±20 V
P_{DISS}	465 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.35 °C/W

PACKAGE STYLE .385X.850 4LFG



1 & 2 = DRAIN 3 & 4 = GATE
5 = SOURCE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{DSS}	I_{DS} = 120 mA V_{GS} = 0 V	65			V
I_{DSS}	V_{DS} = 28 V V_{GS} = 0 V			6.0	mA
I_{GSS}	V_{DS} = 0 V V_{GS} = 30 V			1.0	µA
V_{GS}	I_{DS} = 600 mA V_{GS} = V_{DS}	1.0		7.0	V
gM	V_{DS} = 10 V V_{GS} = 5.0 V		7.2		mho
R_{DSON}	V_{GS} = 20 V I_{DS} = 15 A	5.0			Ω
I_{DSAT}	V_{GS} = 20 V V_{DS} = 10 V		42		A
C_{iss} C_{oss} C_{rss}	V_{DS} = 28 V V_{GS} = 0 V f = 1.0 MHz		300 192 18		pF
G_{ps} η ψ	V_{DS} = 28 V I_{DQ} = 1.2 A P_{out} = 300 W f = 175 MHz	13	 55	 20:1	dB % Relative